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U.S. PATENT DOCUMENTS												
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME		CLASS	SUBCLASS	FILIN	G DATE				
	0,016,383A1	09/23/01	Chen et al.		430	243						
	6,180,490B1	01/30/01	Vassiliev et al.		120	424						
	6,300,172B1	10/09/01	Ang et al.		420	149						
	6,207,530B1	03/27/01	Hsu et al.		43.9	404						
MD	5,851,891	12/22/98	Dawson et al.		439	303						
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	4	FOR	EICN DATE	NT DOCUMEN	TTC							
EXAMINER'S	I	rok	EIGN PAIR	NI DOCUMEN	115	T	Tran	slation				
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)				
	OTHER	ART (Inclu	ding Author	, Title, Date, Per	rtinent P	ages, Etc.)	, t ,					
M	Shallow Trench Isolation, "Trench Isolation," http://courses.nus.edu.sg/course/phy/> pgs. 1-4											
	Institute of Mi	croelectroni	cs - Deep Sub	micron - Ultra-th	in gate o	xides, "Deer	Submic	ron",				
	Institute of Microelectronics - Deep Submicron - Ultra-thin gate oxides, "Deep Submicron", http://www.ime.org.sg/deep/deep_ultra.htm/>, pgs. 1-2											
Max.	SNP Applications/Shallow Trench Isolation (STI), "SNP 9000 Applications", htt://www.surfaceinterface.com/spappsSTI.html>, pgs. 1-2											
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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	OTHER	ART (Inclu	ding Author	, Title, Date, Per	tinent P	ages, Etc.)					
MV	"Ellipsometer/	reflectomete	r for Ultra-th	in Gate Oxide Me	trology,"	October 1,	2001,				
1 1/1	http://www.ecnmag.com/ecnmag/issues/2001/10/>, pg. 1 of 1										
m/X	Hitachi Americ	ca, Ltd. Sem	iconductor E	quipment Group.	, "Cust	omizable Sh	allow Trench				
Jsolation," pg. 1 of 1											
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EXAMINER	11			ATE CONSIDÉR	RED /	1/11/1					
MA MUMM 11/10/05											

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